

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-30V	13mΩ @ V _{GS} = -10V	-9.8A
	25mΩ @ V _{GS} = -4.5V	-7.0A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Backlighting
- Power management functions
- DC-DC converters

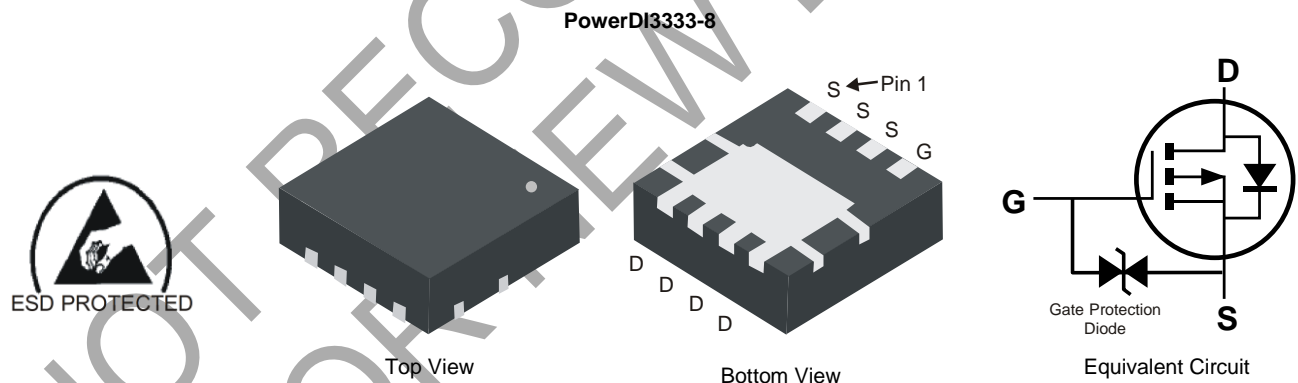
Features and Benefits

- Low R_{DS(ON)} – Ensures On-State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **The DMG7401SFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.0174 grams (Approximate)

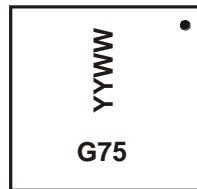


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMG7401SFGQ-7	PowerDI3333-8	2,000	Tape & Reel
DMG7401SFGQ-13	PowerDI3333-8	3,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



G75 = Product Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 22 for 2022)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-30	V	
Gate-Source Voltage	V _{GSS}	±25	V	
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	T _A = +25°C T _A = +70°C	-9.8 -7.7	A
		t < 10s T _A = +25°C T _A = +70°C	-13.5 -10.8	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-3.0	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-80	A	
Avalanche Current (Notes 7 & 8)	I _{AR}	-14	A	
Repetitive Avalanche Energy (Notes 7 & 8) L = 1mH	E _{AR}	104	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P _D	T _A = +25°C	0.94	W
		T _A = +70°C	0.6	
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady State	137	°C/W
		t < 10s	82	°C/W
Total Power Dissipation (Note 6)	P _D	T _A = +25°C	2.2	W
		T _A = +70°C	1.3	
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady State	60	°C/W
		t < 10s	36	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	3.0	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 7. I_{AR} and E_{AR} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1.7	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	9	11	mΩ	V _{GS} = -20V, I _D = -12A
		—	10	13		V _{GS} = -10V, I _D = -9A
		—	17	25		V _{GS} = -4.5V, I _D = -5A
Forward Transfer Admittance	Y _{fs}	—	21	—	S	V _{DS} = -5V, I _D = -10A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	2,246	2,987	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	352	468	pF	
Reverse Transfer Capacitance	C _{rss}	—	294	391	pF	
Gate Resistance	R _g	—	5.1	10	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	20.5	30	nC	V _{DS} = -15V, I _D = -12A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	41	58	nC	
Gate-Source Charge	Q _{gs}	—	7.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	8.0	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	11.3	23	ns	
Turn-On Rise Time	t _r	—	15.4	31	ns	V _{DD} = -15V, V _{GS} = -10V, R _L = 1.25Ω, R _G = 3Ω
Turn-Off Delay Time	t _{D(OFF)}	—	38.0	61	ns	
Turn-Off Fall Time	t _f	—	22.0	38	ns	
BODY DIODE CHARACTERISTICS						
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
Reverse Recovery Time (Note 9)	t _{RR}	—	20	31	ns	I _S = -9.5A, dI/dt = 100A/μs
Reverse Recovery Charge (Note 9)	Q _{RR}	—	9.5	18	nC	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

NOT RECOMMENDED FOR NEW DESIGN

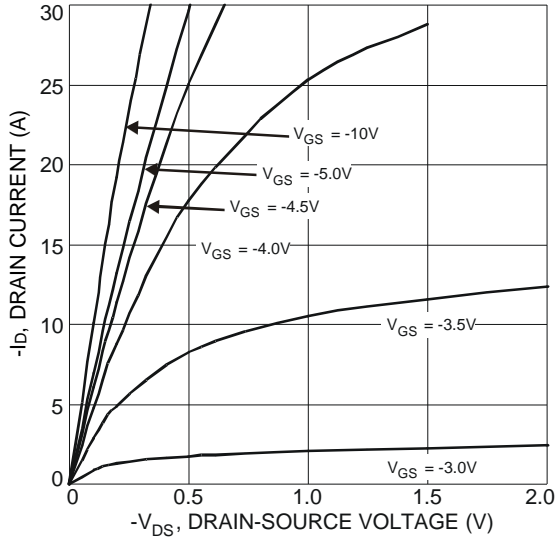


Fig. 1 Typical Output Characteristics

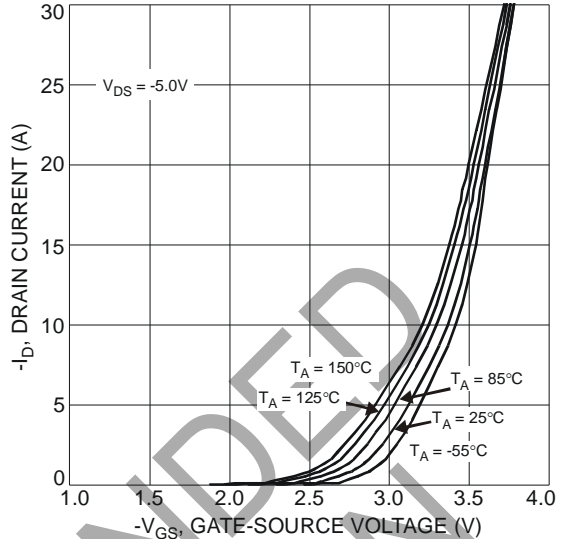


Fig. 2 Typical Transfer Characteristics

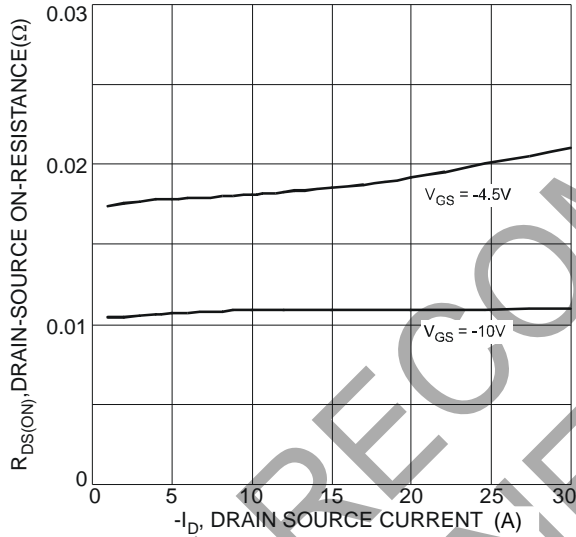


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

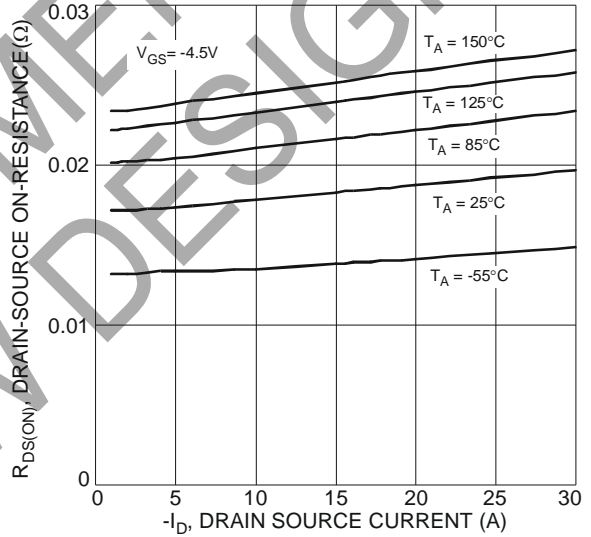


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

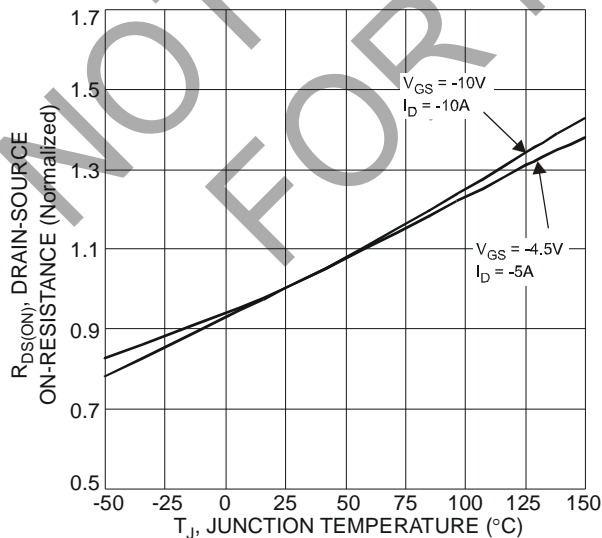


Fig. 5 On-Resistance Variation with Temperature

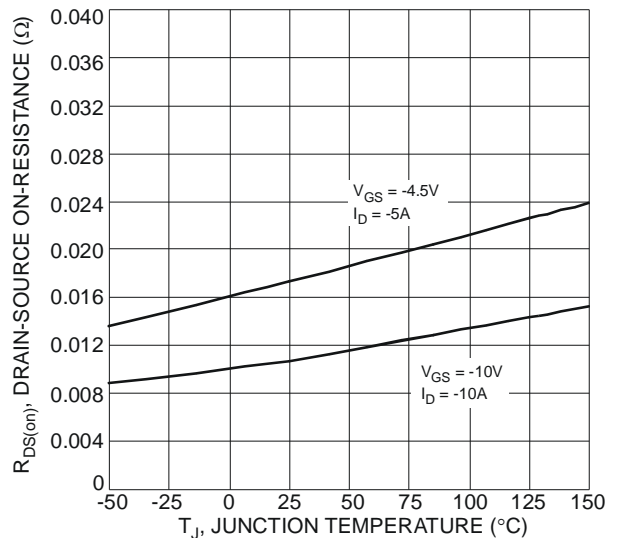


Fig. 6 On-Resistance Variation with Temperature

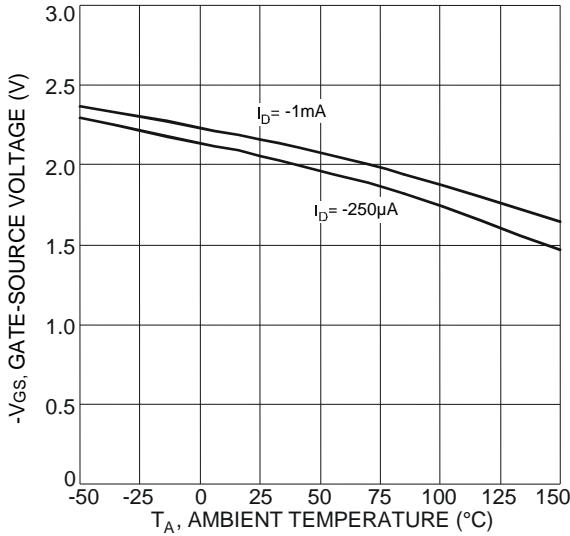


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

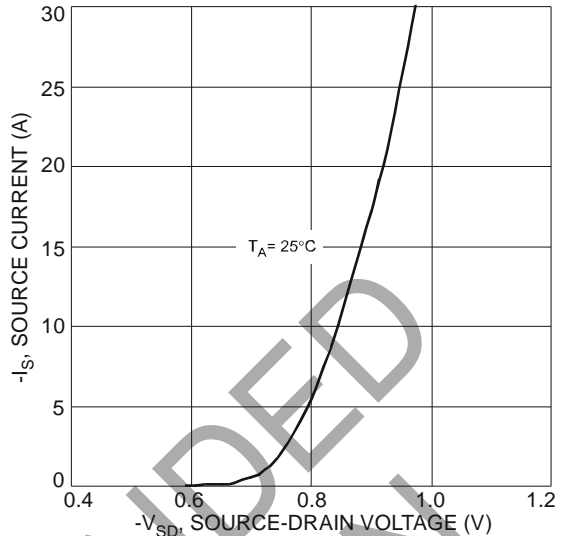


Fig. 8 Diode Forward Voltage vs. Current

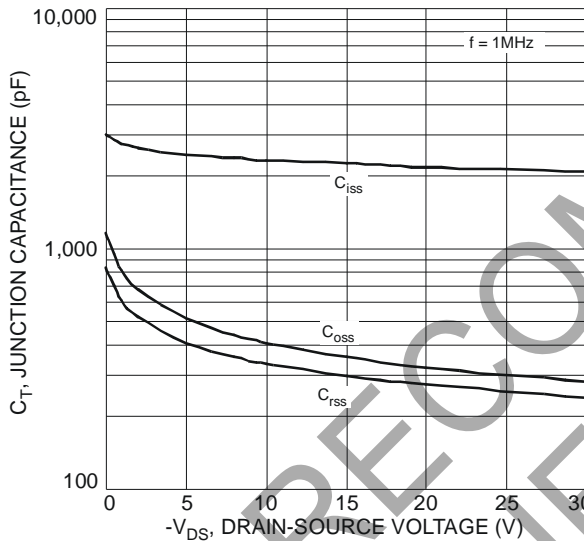


Fig. 9 Typical Junction Capacitance

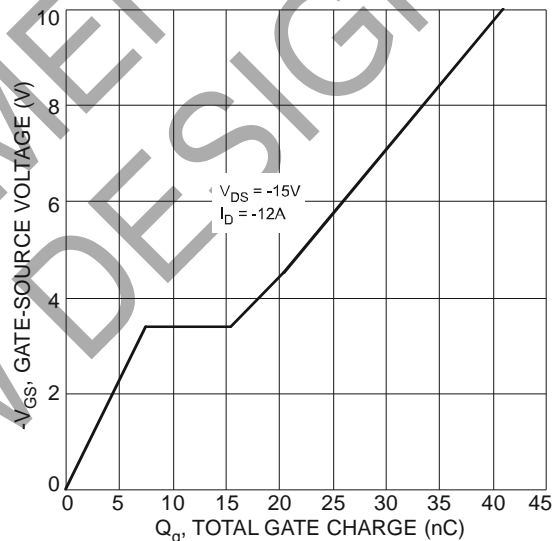


Fig. 10 Gate-Charge Characteristics

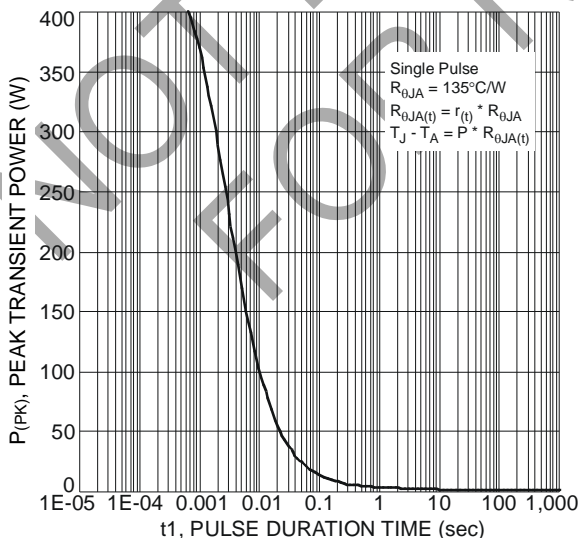


Fig. 11 Single Pulse Maximum Power Dissipation

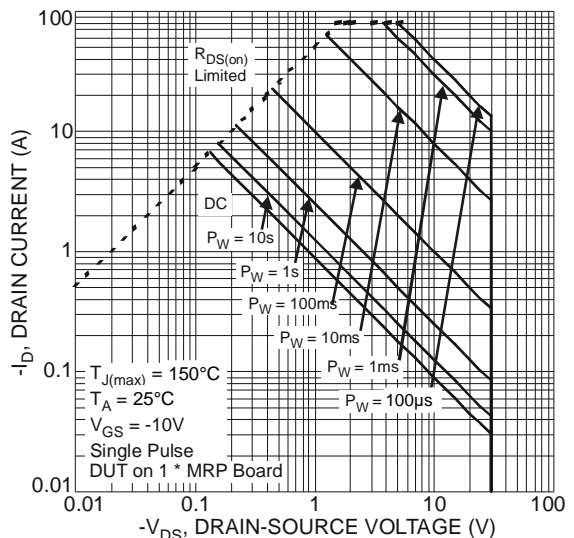
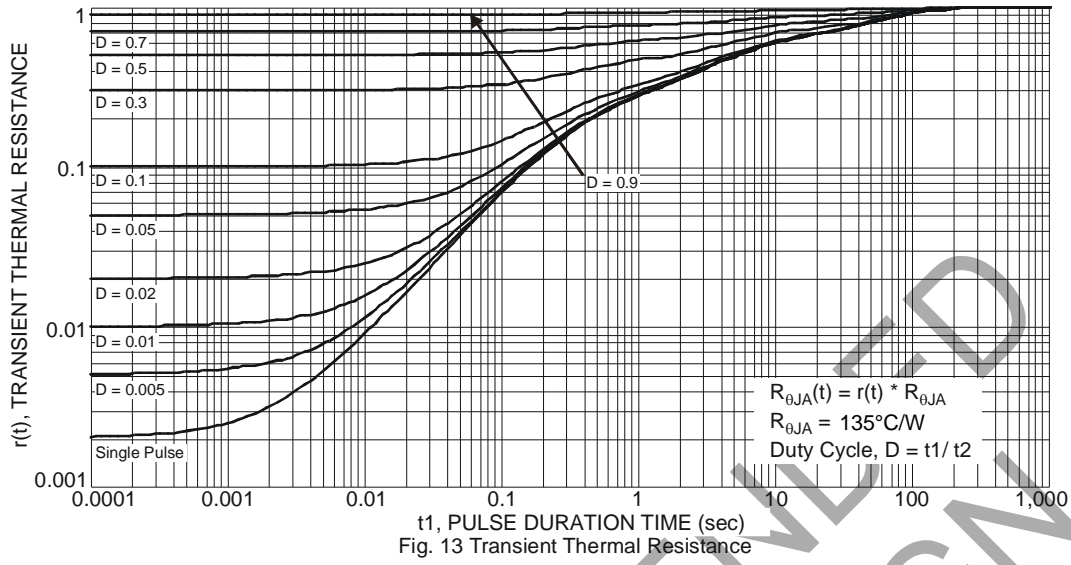


Fig. 12 SOA, Safe Operation Area

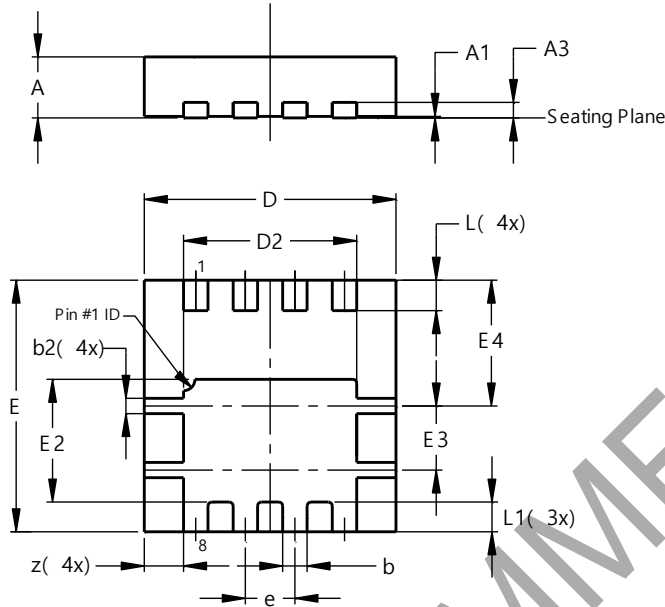


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Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8

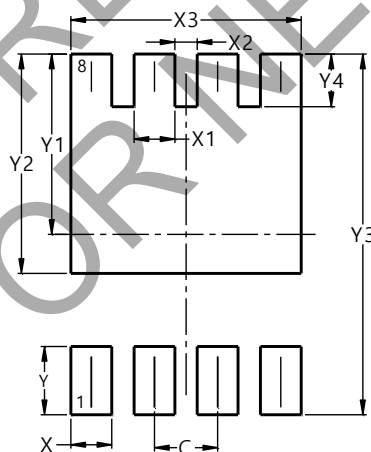


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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